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(54) **Title**: METHOD OF FORMING AN INDIUM-CONTAINING TRANSPARENT CONDUCTIVE OXIDE FILM, METAL TARGETS USED IN THE METHOD AND PHOTOVOLTAIC DEVICES UTILIZING SAID FILMS

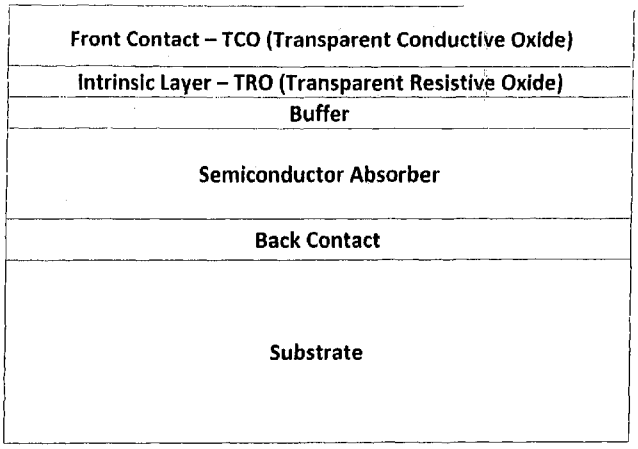

Figure 1

(57) **Abstract**: A method of forming an indium-containing transparent conductive oxide by reactive sputtering a metal target containing indium in an oxygen containing atmosphere and then depositing the resulting indium oxide on a substrate. Metal targets used in the method and photovoltaic devices utilizing the transparent conductive oxides are also disclosed.